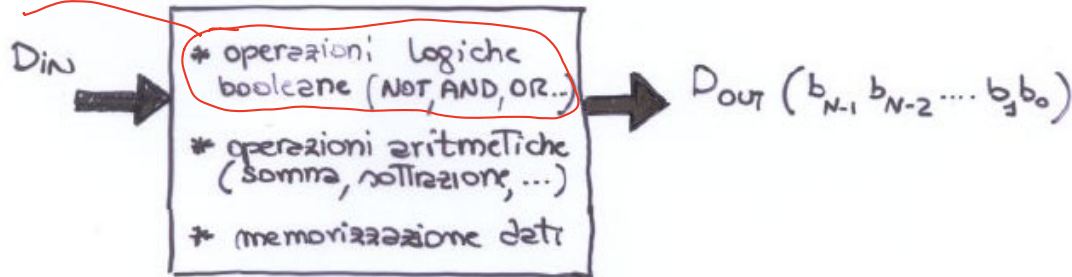


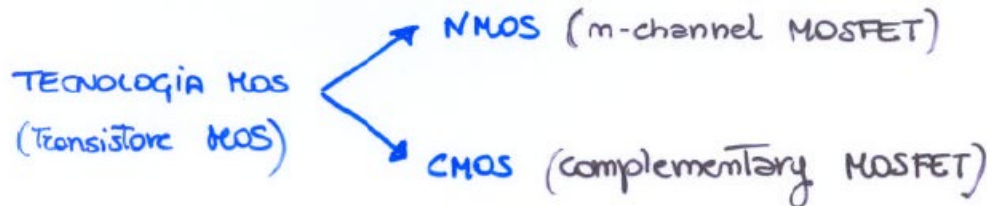
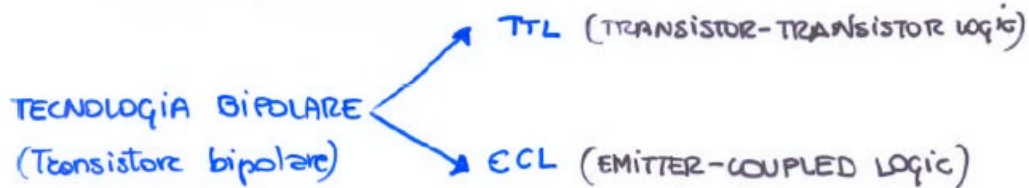
LOGICA CMOS

* SISTEMA DIGITALE

IN QUESTO CORSO



* FAMIGLIE LOGICHE

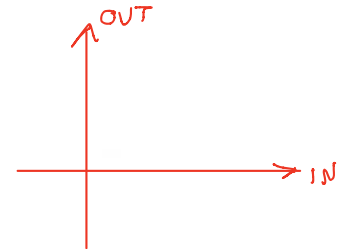


COME SI ANALIZZA UNA PORTA LOGICA?

1. funzione logica svolta

$$y = f(A, B, C, \dots)$$

2. Caratteristica ingresso-uscita



3. Dissipazione di potenza

4. Velocità di risposta

} PRODOTTO
(RITARDO x CONSUMO)

INVERTITORE LOGICO (NOT GATE)

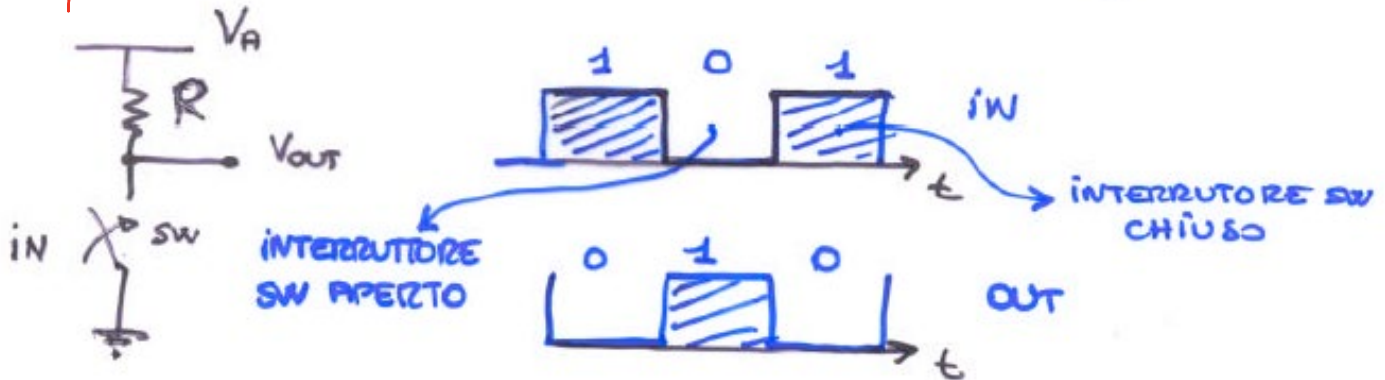


simbolo elettrico

iN	OUT
0	1
1	0

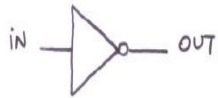
funzione logica

esempio



INVERTITORE LOGICO (NOT GATE)

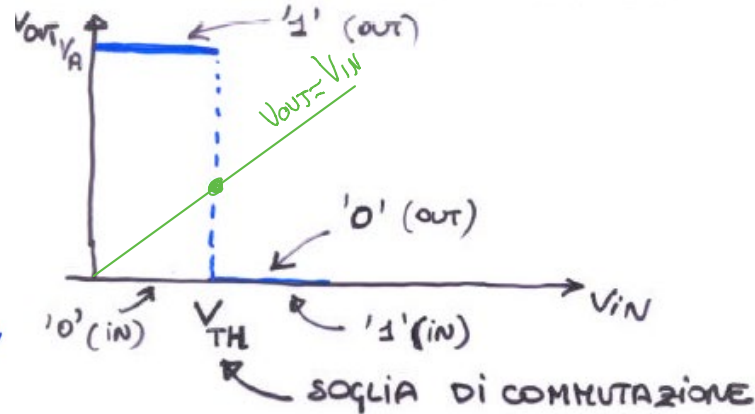
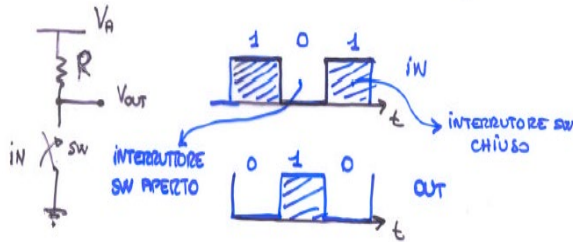
→ CARATTERISTICA DI TRASFERIMENTO "IDEALE"



simbolo elettrico

IN	OUT
0	1
1	0

funzione logica

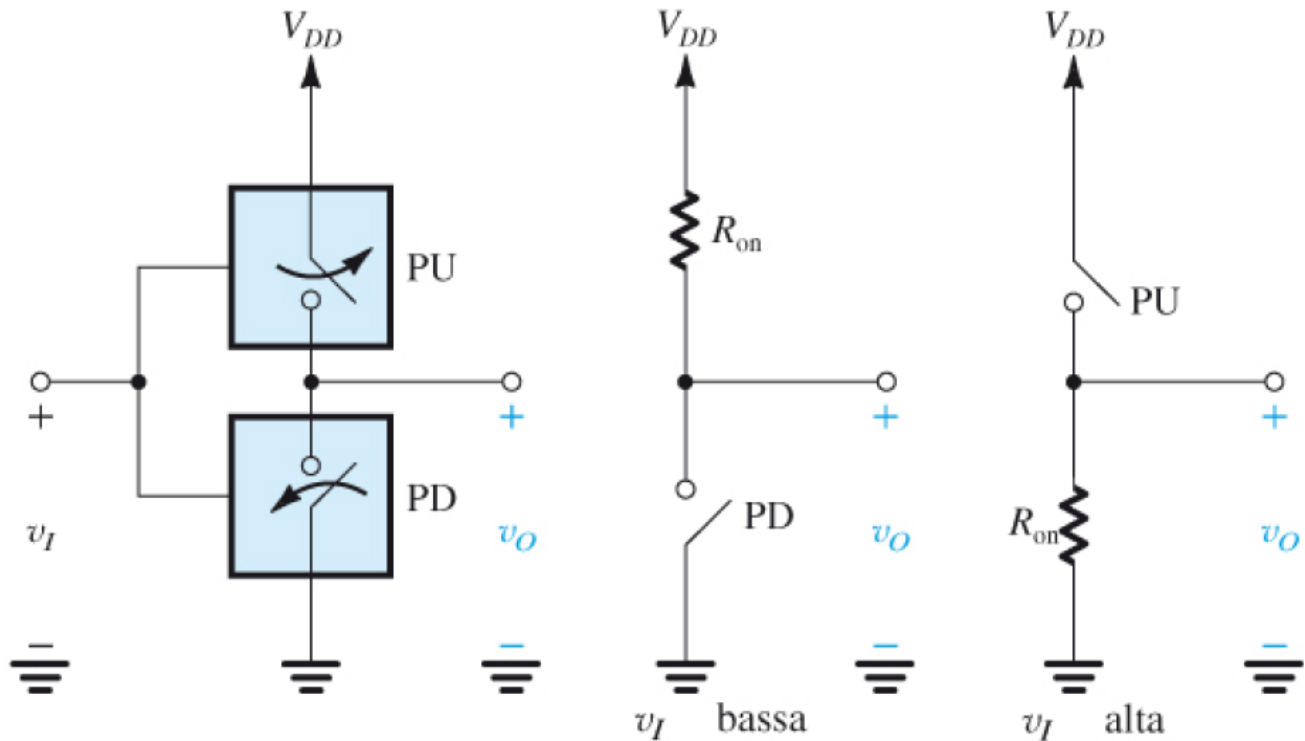


- $V_{IN} < V_{TH} \Rightarrow$ SW APERTO $\Rightarrow I_R = 0 \doteq I_H$
 $\hookrightarrow V_{OUT} = V_A - R I_R' = V_A$
- $V_{IN} > V_{TH} \Rightarrow$ SW CHIUSO \Rightarrow USCITA CORTOCIRCUITATA A MASSA
 $\hookrightarrow V_{OUT} = 0 ; I_R = \frac{V_A}{R} \doteq I_L$

↓
DISSIPAZIONE DI POTENZA STATICA

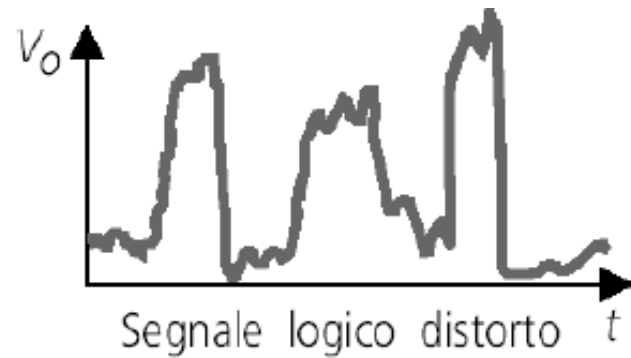
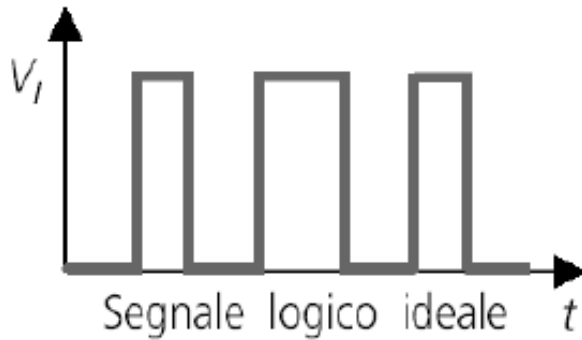
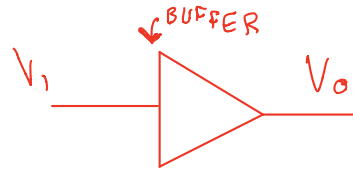
$$P_{STAT} = V_A \frac{I_L + I_H}{2} = \frac{1}{2} V_A^2 \frac{1}{R}$$

INVERTITORE LOGICO A 2 INTERRUTTORI



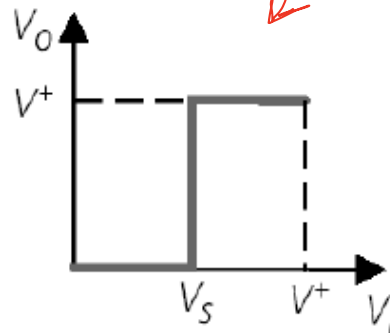
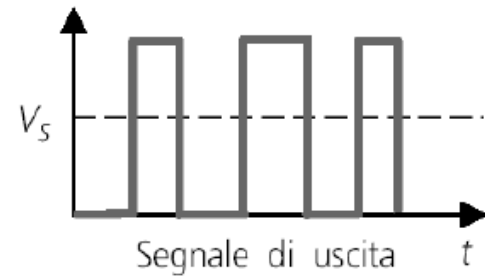
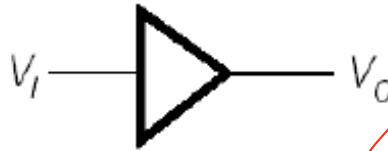
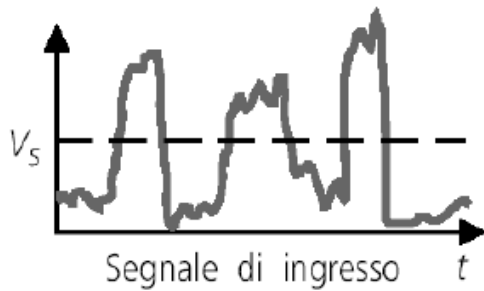
- ✓ La rete di pull-up e' costituita da un interruttore controllato in tensione che si chiude quando V_I e' bassa. La rete di pull-down e' costituita da un interruttore controllato in tensione che si apre quando V_I e' bassa.
- ✓ La dissipazione di potenza statica e' nulla

SEGNALE LOGICO



BUFFER LOGICO

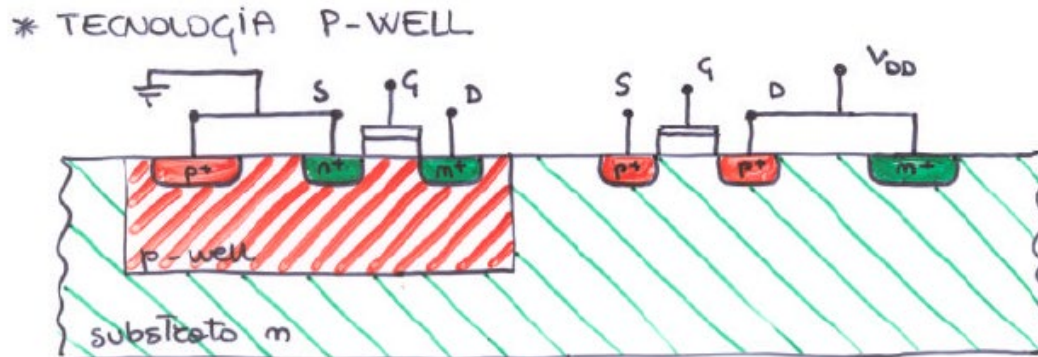
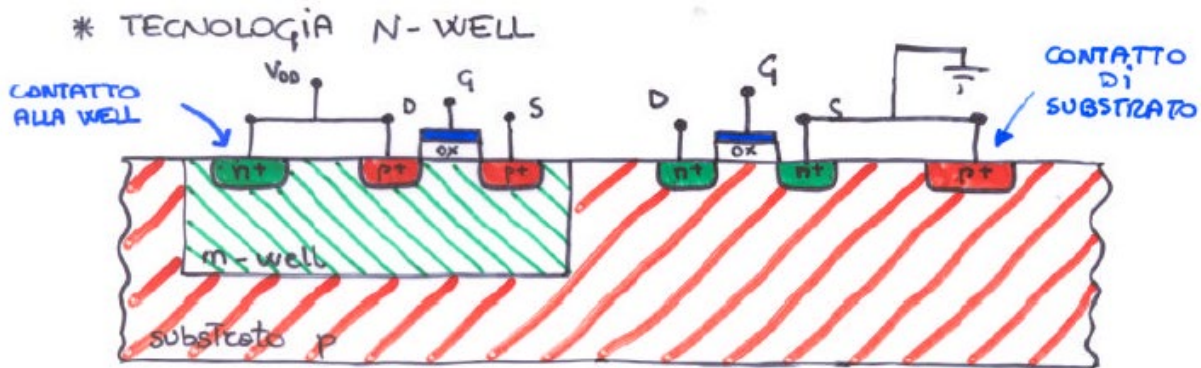
rigenerazione dei livelli logici



Caratteristica di trasferimento

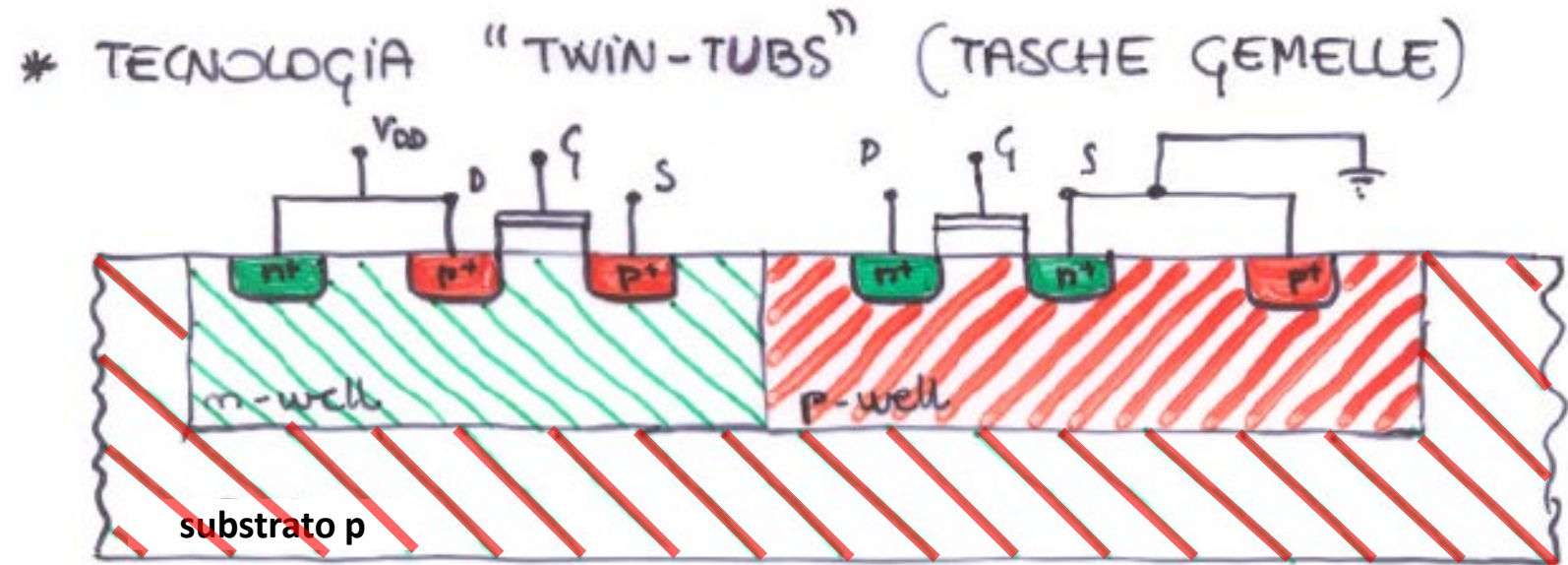
TECNOLOGIE CMOS

(Complementary Metal Oxide Silicon)



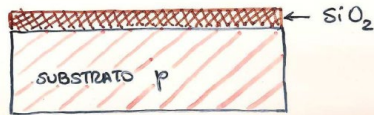
TECNOLOGIE CMOS

(Complementary Metal Oxide Silicon)



TECNOLOGIA DI FABBRICAZIONE DI CIRCUITI INTEGRATI - PROCESSO CMOS

1) OSSIDAZIONE DEL WAFER DI SILICIO (mediante processo termico)



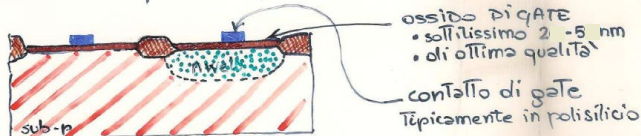
2) REALIZZAZIONE DELLA "TASCA" n^- (N-WELL)



3) OSSIDAZIONE SELETTIVA per definire le regioni dei diversi dispositivi



4) OSSIDAZIONE DI GATE E REALIZZAZIONE DEL CONTATTO DI GATE

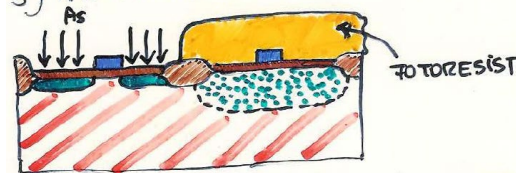


ossido di gate
• sottilissimo 2 - 5 nm
• di ottima qualità

5) IMPIANTAZIONE DEI SOURCE E DRAIN DI TIPO P



5) IMPIANTAZIONE DEI SOURCE E DRAIN DI TIPO N



6) STRUTTURA FINALE CON LE METALLIZZAZIONI

